

ABSTRACT

PLASMA ETCHING METHOD

The present invention is a plasma etching method comprising subjecting a silicon-containing film to plasma etching using a process gas, the process gas
5 comprising a linear saturated fluorohydrocarbon compound represented by a formula (1),
and a gaseous fluorine-containing compound (excluding the compound represented by
the formula (1)) that functions as a fluorine radical source under plasma etching
conditions, wherein x represents 3 or 4, y represents an integer from 5 to 9, and z
represents an integer from 1 to 3. The present invention provides a plasma etching
10 method that can selectively etch the silicon-containing film with respect to the mask,
and form a hole or a trench having a good shape within a short time.

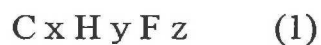


FIG. 1